

PMDT290UNE

20 V, 800 mA dual N-channel Trench MOSFET Rev. 1 — 13 September 2011

Product data sheet

1. **Product profile**

1.1 General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in an ultra small and flat lead SOT666 Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Very fast switching
- Trench MOSFET technology
- ESD protection up to 2 kV
- AEC-Q101 qualified

1.3 Applications

- Relay driver
- High-speed line driver

- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	or						
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	20	V
V_{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	<u>[1]</u>	-	-	800	mΑ
Static charac	cteristics (per transistor)						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 500 \text{ mA}; T_j = 25 \text{ °C}$		-	290	380	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		D4 D0
2	G1	gate TR1	6 5 4	D1 D2
3	D2	drain TR2		
4	S2	source TR2	0	G1 $G2$
5	G2	gate TR2	1 2 3	
6	D1	drain TR1	SOT666	S1 S2 017aaa256

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMDT290UNE	-	plastic surface-mounted package; 6 leads	SOT666

4. Marking

Table 4. Marking codes

Type number	Marking code
PMDT290UNE	AE

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor					
V_{DS}	drain-source voltage	T _j = 25 °C		-	20	V
V_{GS}	gate-source voltage			-8	8	V
I_D	drain current	$V_{GS} = 4.5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$	<u>[1]</u>	-	800	mΑ
		$V_{GS} = 4.5 \text{ V}; T_{amb} = 100 ^{\circ}\text{C}$	<u>[1]</u>	-	500	mΑ
I _{DM}	peak drain current	$T_{amb} = 25 ^{\circ}C$; single pulse; $t_p \le 10 \mu s$		-	3.2	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	330	mW
			<u>[1]</u>	-	390	mW
		T _{sp} = 25 °C		-	1090	mW
Per device						
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	500	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C

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 Table 5.
 Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
T _{stg}	storage temperature			-65	150	°C
Source-drai	n diode					
Is	source current	T _{amb} = 25 °C		-	370	mΑ
ESD maxim	um rating					
V _{ESD}	electrostatic discharge voltage	HBM	[3]	-	2000	V

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

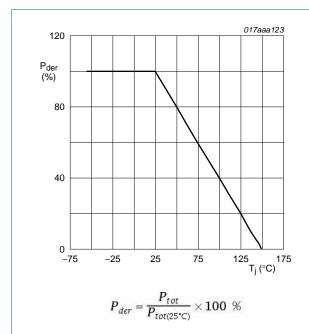


Fig 1. Normalized total power dissipation as a function of junction temperature

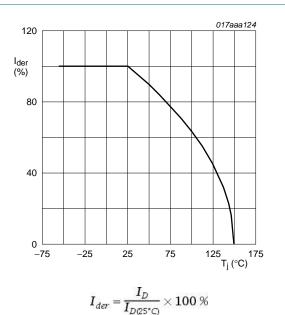
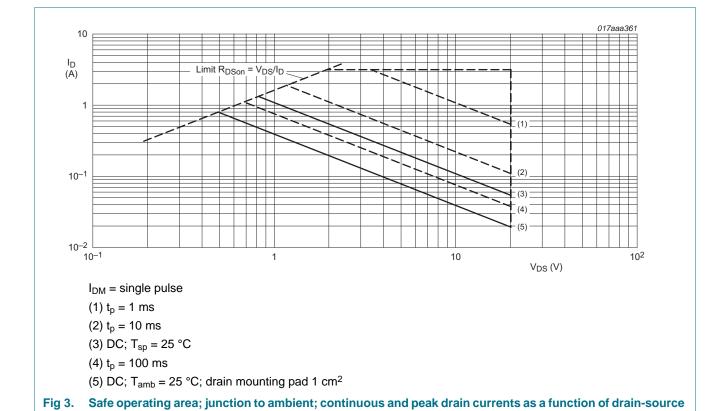


Fig 2. Normalized continuous drain current as a function of junction temperature



6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance	in free air	<u>[1]</u>	-	330	380	K/W
	from junction to ambient		[2]	-	280	320	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	115	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	ū	-	-	250	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

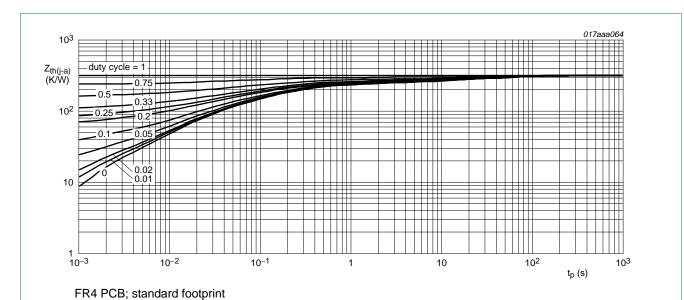


Fig 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

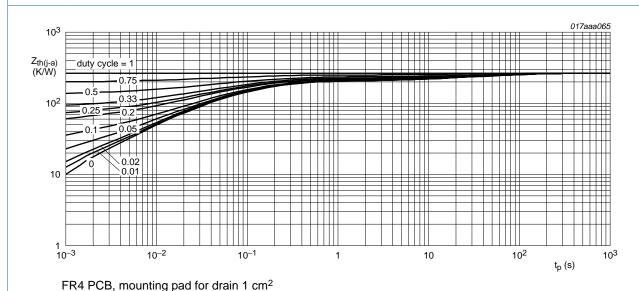


Fig 5. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics (per transistor)					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.5	0.75	0.95	V
I _{DSS}	drain leakage current	$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	10	μΑ
I_{GSS}	gate leakage current	$V_{GS} = 8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	2	μΑ
		$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	2	μΑ
		$V_{GS} = 4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	500	nA
		$V_{GS} = -4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	500	nΑ
R _{DSon}	drain-source on-state	V_{GS} = 4.5 V; I_D = 500 mA; T_j = 25 °C	-	290	380	mΩ
	resistance	$V_{GS} = 4.5 \text{ V}; I_D = 500 \text{ mA}; T_j = 150 \text{ °C}$	-	460	610	mΩ
		$V_{GS} = 2.5 \text{ V}; I_D = 400 \text{ mA}; T_j = 25 \text{ °C}$	-	420	620	mΩ
		V_{GS} = 1.8 V; I_D = 100 mA; T_j = 25 °C	-	600	1100	$\text{m}\Omega$
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 200 \text{ mA}; T_j = 25 \text{ °C}$	-	1.6	-	S
Dynamic	characteristics (per transist	or)				
Q _{G(tot)}	total gate charge	$V_{DS} = 10 \text{ V}; I_D = 500 \text{ mA}; V_{GS} = 4.5 \text{ V};$	-	0.45	0.68	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.15	-	nC
Q_{GD}	gate-drain charge		-	0.15	-	nC
C _{iss}	input capacitance	$V_{DS} = 10 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	55	83	pF
C _{oss}	output capacitance	T _j = 25 °C	-	15	-	pF
C _{rss}	reverse transfer capacitance		-	7	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 10 V; R_L = 250 Ω ; V_{GS} = 4.5 V;	-	6	12	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	4	-	ns
t _{d(off)}	turn-off delay time		-	86	172	ns
t _f	fall time		-	31	-	ns
Source-d	rain diode (per transistor)					
V _{SD}	source-drain voltage	$I_S = 300 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	0.48	0.77	1.2	V

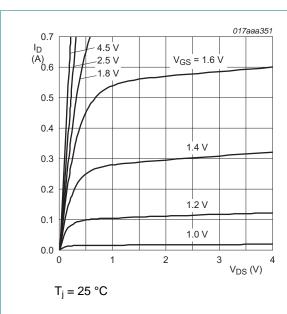
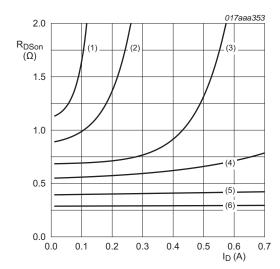


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



T_j = 25 °C

(1) $V_{GS} = 1.3 \text{ V}$

(2) $V_{GS} = 1.4 \text{ V}$

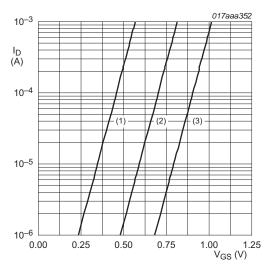
(3) $V_{GS} = 1.6 \text{ V}$

(4) $V_{GS} = 1.8 \text{ V}$

(5) $V_{GS} = 2.5 \text{ V}$

(6) $V_{GS} = 4.5 \text{ V}$

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



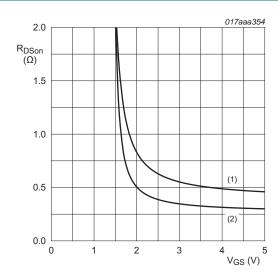
 $T_j = 25 \, ^{\circ}C; \, V_{DS} = 5 \, V$

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage



 $I_D = 400 \text{ mA}$

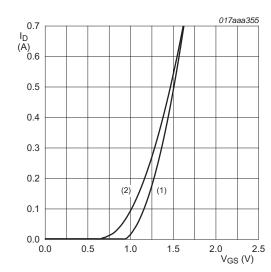
(1) $T_i = 150 \, ^{\circ}C$

(2) $T_i = 25 \, ^{\circ}C$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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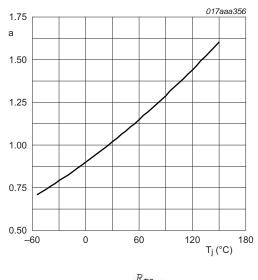


 $V_{DS} > I_D \times R_{DSon}$

(1)
$$T_j = 25 \, ^{\circ}C$$

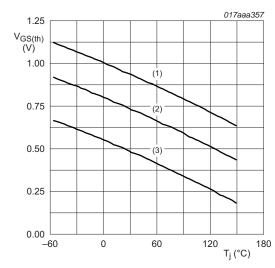
(2) $T_i = 150 \, ^{\circ}\text{C}$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$

Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



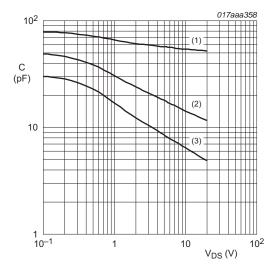
 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

(1) maximum values

(2) typical values

(3) minimum values

Fig 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

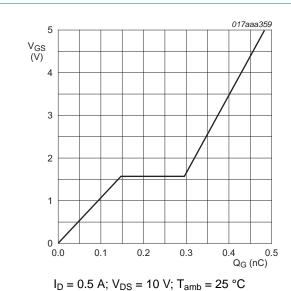
(1) C_{iss}

(2) C_{oss}

(3) C_{rss}

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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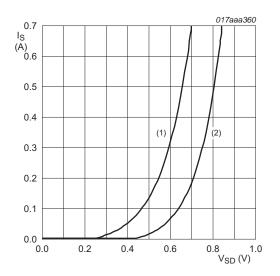


1D = 0.5 A, VDS = 10 V, Tamb = 25 C

V_{DS} — V_{GS(pl)} V_{GS(th)} V_{GS} Q_{GS1} Q_{GS2} Q_{G(tot)} Q_{GG} Q_{G(tot)} 017aaa137

Fig 15. Gate charge waveform definitions





 $V_{GS} = 0 V$

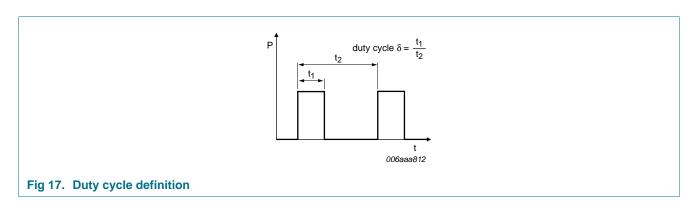
(1) $T_j = 150 \, ^{\circ}\text{C}$

(2) $T_j = 25 \, ^{\circ}C$

Fig 16. Source current as a function of source-drain voltage; typical values

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8. Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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9. Package outline

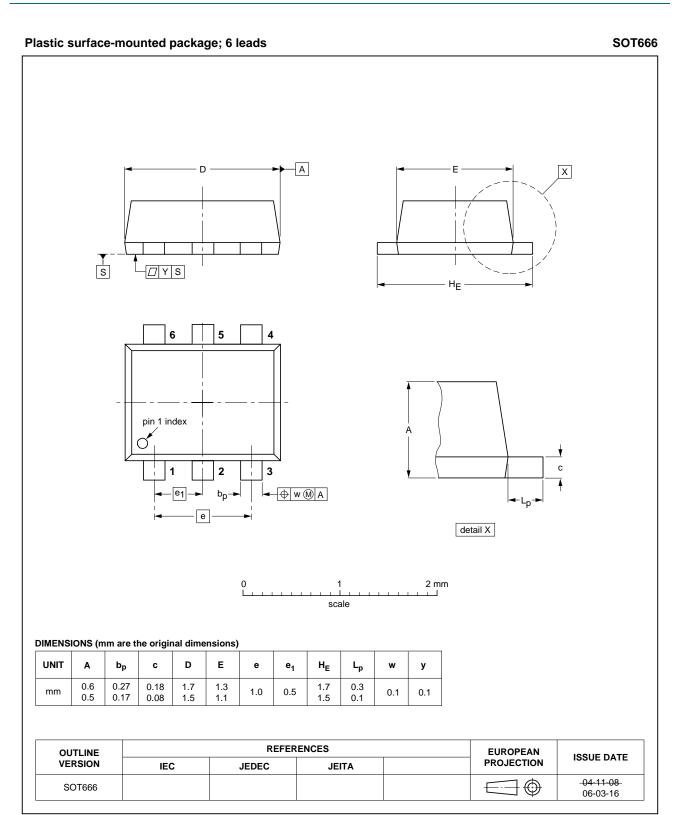
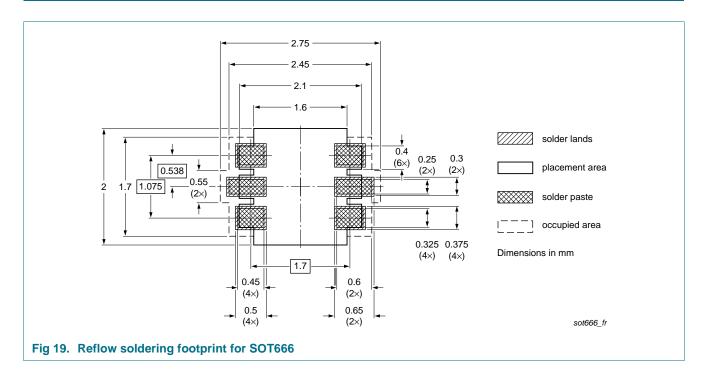


Fig 18. Package outline SOT666

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10. Soldering



11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMDT290UNE v.1	20110913	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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